



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25°C
-20V	5.5Ω @ $V_{GS} = -4.5V$	-200mA
	7.5Ω @ $V_{GS} = -2.5V$	-170mA

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions

Features

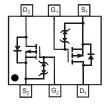
- Dual P-Channel MOSFET
- Low On-Resistance
 - 5.5Ω @ -4.5V
 - 7.5Ω @ -2.5V
 - 11.5Ω @ -1.8V
 - 17.5Ω @ -1.5V
- Very Low Gate Threshold Voltage V_{GS(TH)} <1.15V
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT963
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.0027 grams (Approximate)







Top View

Internal Schematic

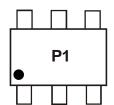
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP210DUDJ-7	SOT963	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, see http://www.diodes.com/products/packages.html.

Marking Information (Note 5)



P1 = Product Type Marking Code

Note: 5. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

DMP210DUDJ
Document number: DS31494 Rev. 10 - 2

1 of 6

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Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±8	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-200 -150	mA
Continuous Drain Current (Note 6) V _{GS} = -2.5V	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-170 -130	mA
Pulsed Drain Current	$T_{P} = 10 \mu s$	I _{DM}	-600	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	P _D	330	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{OJA}	377.16	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

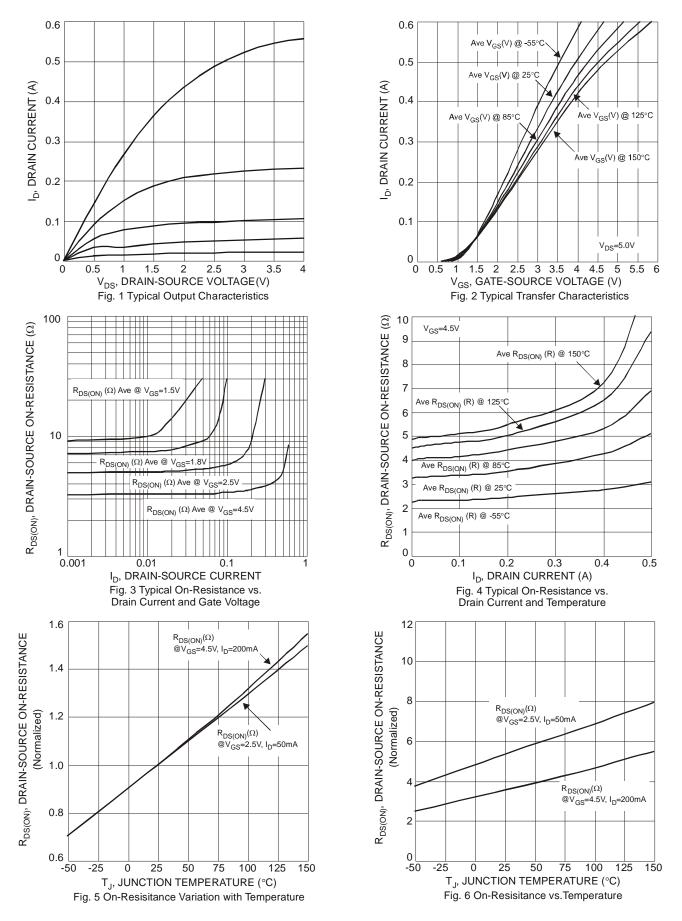
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zana Oata Valtana Basin Oamani	I _{DSS}	_	_	-100	nA	V _{DS} = -16V, V _{GS} = 0V
Zero Gate Voltage Drain Current				-50	nA	$V_{DS} = -5.0V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 5.0V, V_{DS} = 0V$
•				±1	μA	$V_{GS} = \pm 8.0V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.45		-1.15	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			_	5.5		$V_{GS} = -4.5V$, $I_{D} = -100mA$
				7.5		$V_{GS} = -2.5V, I_D = -50mA$
Static Drain-Source On-Resistance	R _{DS(ON)}			11.5	Ω	$V_{GS} = -1.8V, I_D = -20mA$
			_	17.5		$V_{GS} = -1.5V, I_D = -10mA$
			20	_		$V_{GS} = -1.2V, I_D = -1mA$
Forward Transfer Admittance	Y _{fs}		200	_	mS	$V_{DS} = -10V$, $I_{D} = -0.2A$
Diode Forward Voltage (Note 7)	V_{SD}	-0.5		-1.2	V	$V_{GS} = 0V, I_{S} = -115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}		13.72	27.44	pF	4514.14
Output Capacitance	Coss		4.01	8.02	pF	$V_{DS} = -15V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	2.34	4.68	pF	
SWITCHING CHARACTERISTICS (Note 8)						
Turn-On Delay Time	t _{d(on)}	_	7.7	_		V _{GS} = -4.5V, V _{DD} = -15V
Rise Time	t _r	_	19.3	_		
Turn-Off Delay Time	t _{d(off)}	_	25.9	_	ns	$I_D = -180 \text{mA}, R_G = 2.0 \Omega$
Fall Time	t _f		31.5	_		

Notes:

- 6. Device mounted on 1" \times 1" FR-4 substrate PCB, with minimum recommended pad layout, single sided. 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.







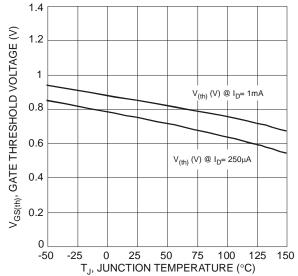
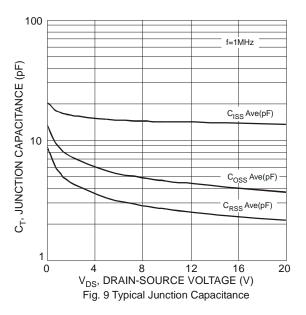


Fig. 7 Gate Threshold Variation vs. Ambient Temperature



0.6

0.5

V_{SD} (V) @ V_{GS}=0V

T_A=25°C

0.1

0.2

0.4

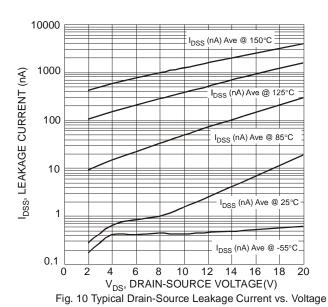
0.6

0.8

1.2

V_{SD}, SOURCE-DRAIN VOLTAGE (V)

Fig. 8 Diode Forward Voltage vs. Current

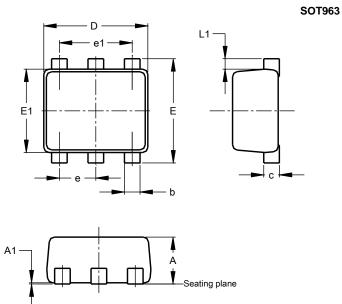


r(t) @ D=0.5 r(t), Transient Thermal Resistance r(t) @ D=0.3 0.1 r(t) @ D=0.1 r(t) @ D=0.05 ШЩЦ r(t) @ D=0.02 0.01 r(t) @ D=0.01 r(t) @ D=0.005 Rthja (t)=r(t) *Rthja Rthja=369C/W Duty Cycle, D=t1/t2 r(t) @ D=Single Pulse 0.001 0.00001 0.0001 0.001 0.1 100 1000 t1, Pulse Duration Time (sec) Fig. 11 Transient Thermal Resistance



Package Outline Dimensions

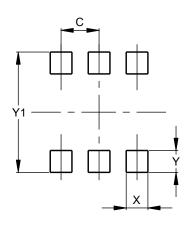
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT963					
Dim	Min	Max	Тур		
Α	0.40	0.50	0.45		
A1	0.00	0.05	_		
b	0.10	0.20	0.15		
С	0.120	0.180	0.150		
D	0.95	1.05	1.00		
Е	0.95	1.05	1.00		
E1	0.75	0.85	0.80		
е	_	_	0.35		
e1	_	_	0.70		
L1	0.05	0.15	0.10		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT963

Dimensions	Value (in mm)		
С	0.350		
Х	0.200		
Y	0.200		
Y1	1.100		



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DMP210DUDJ 6 of 6

Document number: DS31494 Rev. 10 - 2

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